

P-Channel Enhancement Mode MOSFET

GENERAL DESCRIPTION

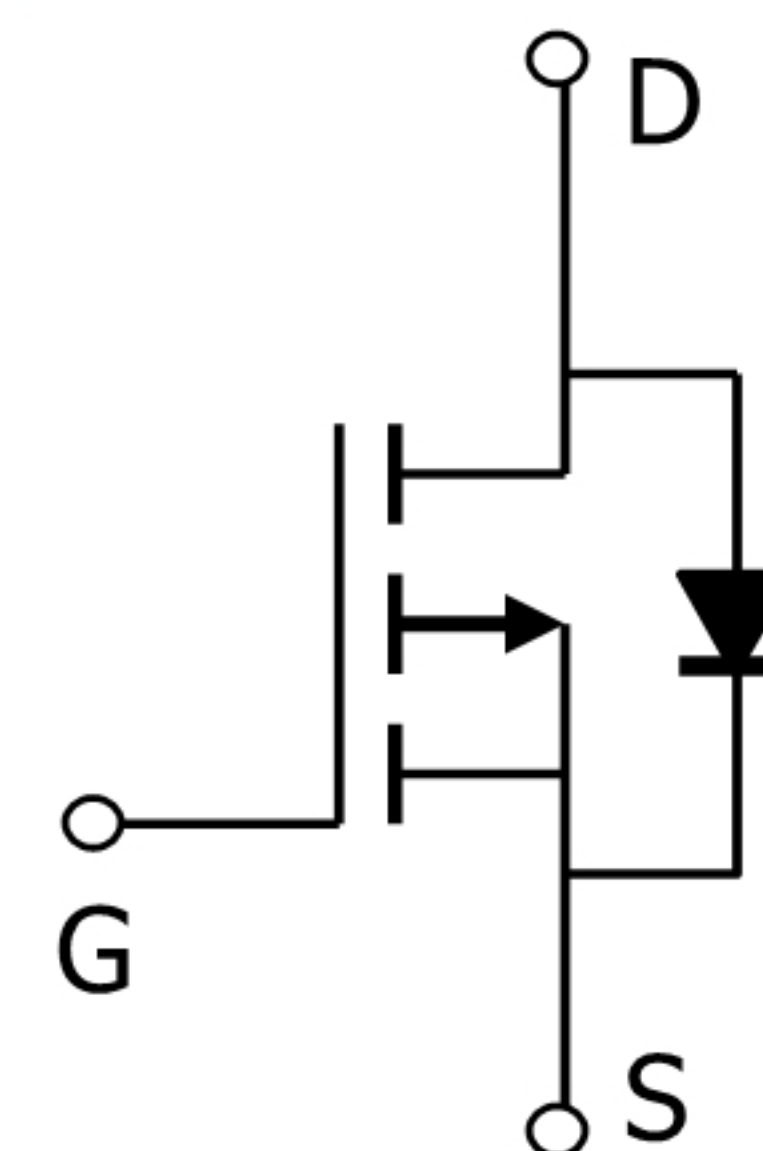
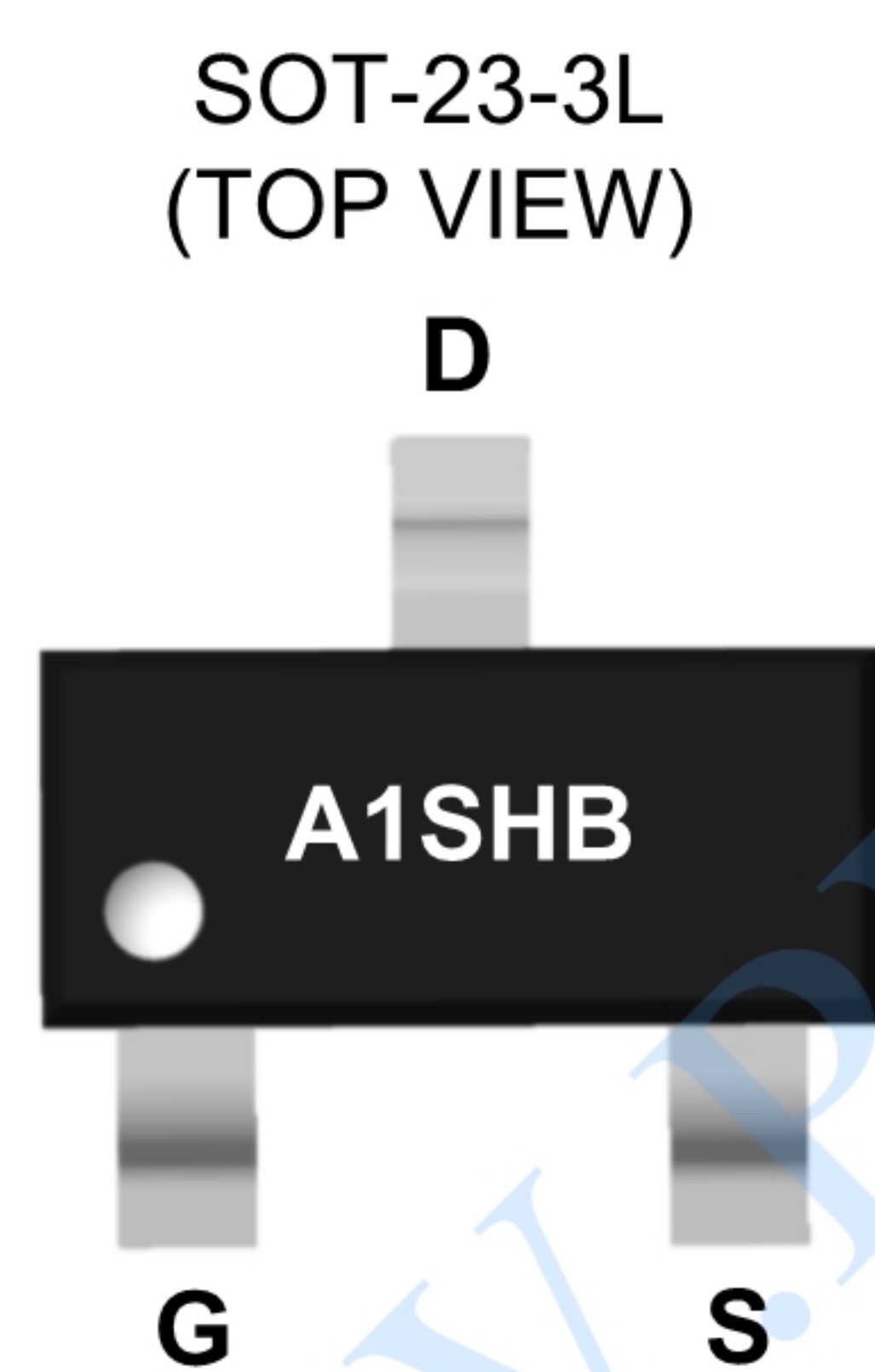
The PW2301A uses advanced trench It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications .

FEATURES

$V_{DS} = -20V$, $I_D = -3A$

$R_{DS(ON)} < 110m\Omega$ @ $V_{GS}=4.5V$

Available in a 3-Pin SOT23-3 Package



Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	-3	A
Drain Current - Pulsed (Note 1)	I_{DM}	-10	A
Maximum Power Dissipation	P_D	1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	125	°C/W
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ELECTRICAL CHARACTERISTICS

(TA = 25°C, unless otherwise noted.)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D = -250μA	-20	-24	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20V,V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D = -250μA	-0.4	-0.7	-1	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = -4.5V, I _D = -3A	-	64	110	mΩ
		V _{GS} = -2.5V, I _D = -2A		89	140	mΩ
Forward Transconductance	g _{FS}	V _{DS} = -5V,I _D = -2A	5	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} = -10V,V _{GS} =0V, F=1.0MHz	-	405	-	PF
Output Capacitance	C _{oss}		-	75	-	PF
Reverse Transfer Capacitance	C _{rss}		-	55	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} = -10V,I _D = -1A V _{GS} = - 4.5V,R _{GEN} =10Ω	-	11	-	nS
Turn-on Rise Time	t _r		-	35	-	nS
Turn-Off Delay Time	t _{d(off)}		-	30	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} = -10V,I _D = -3A, V _{GS} = -2.5V	-	3.3	12	nC
Gate-Source Charge	Q _{gs}		-	0.7	-	nC
Gate-Drain Charge	Q _{gd}		-	1.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =1.3A	-	-	-1.2	V
Diode Forward Current (Note 2)	I _S	-	-	-	-3	A

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

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Typical Electrical and Thermal Characteristics

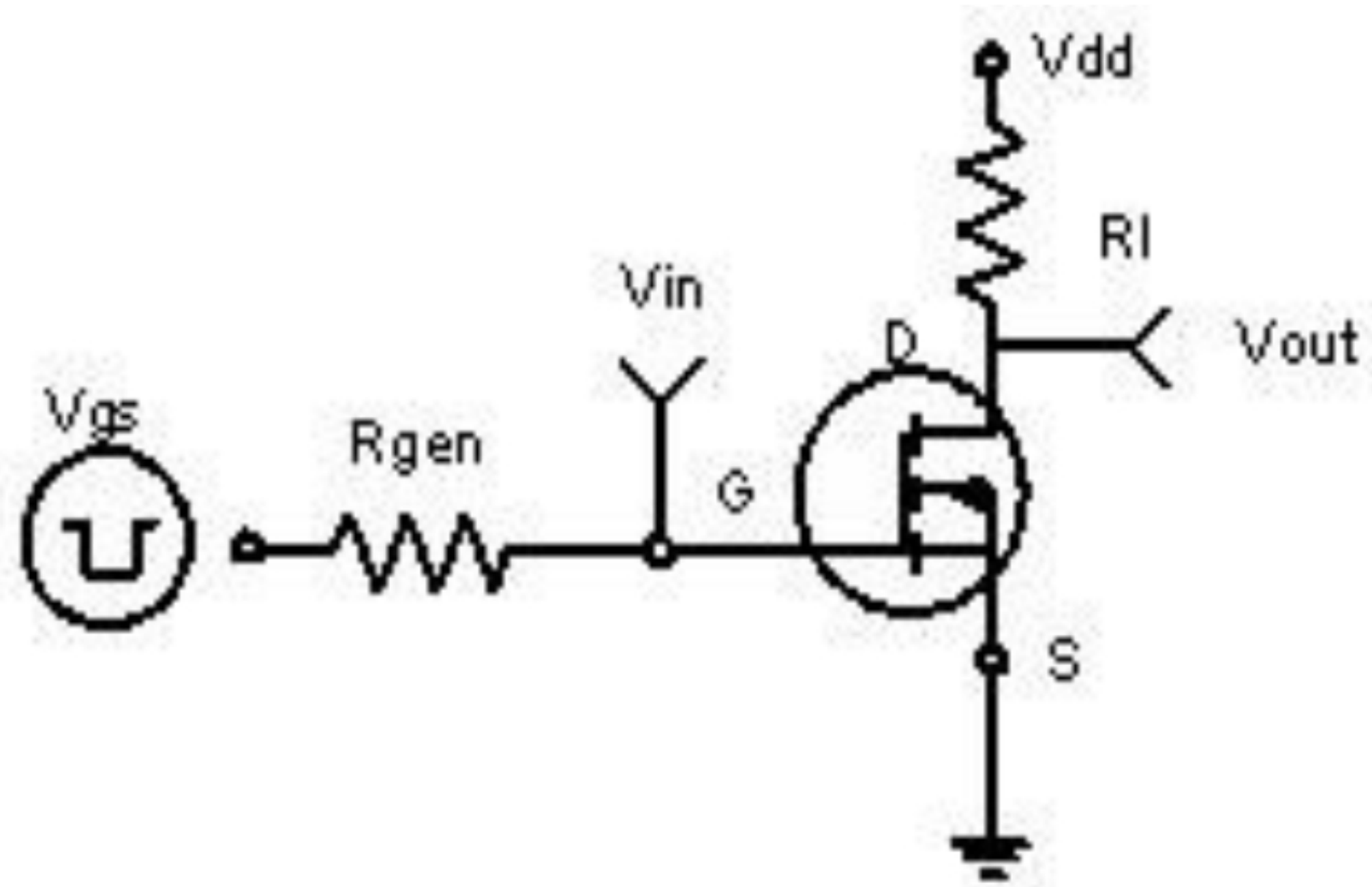


Figure 1: Switching Test Circuit

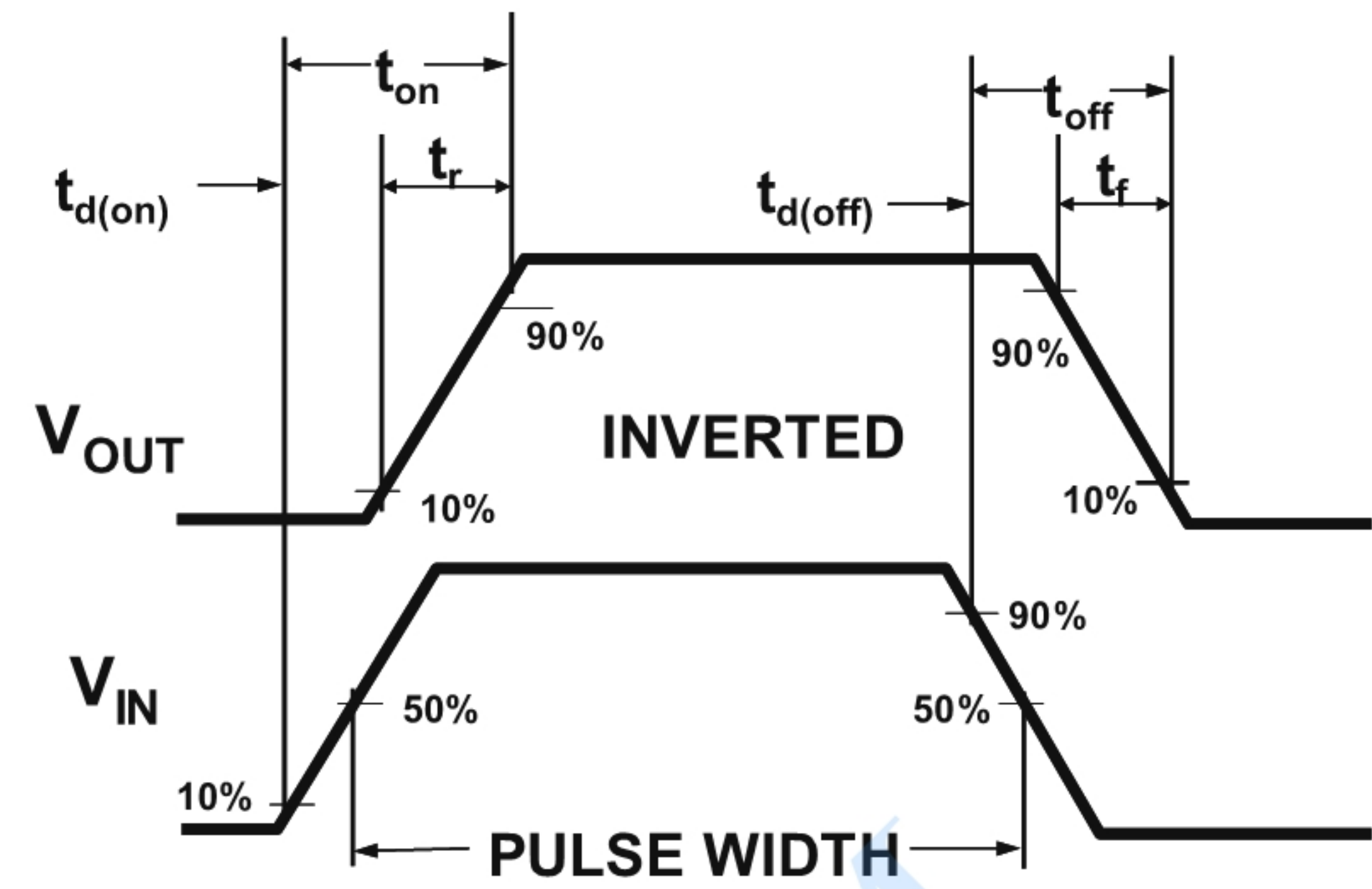


Figure 2: Switching Waveforms

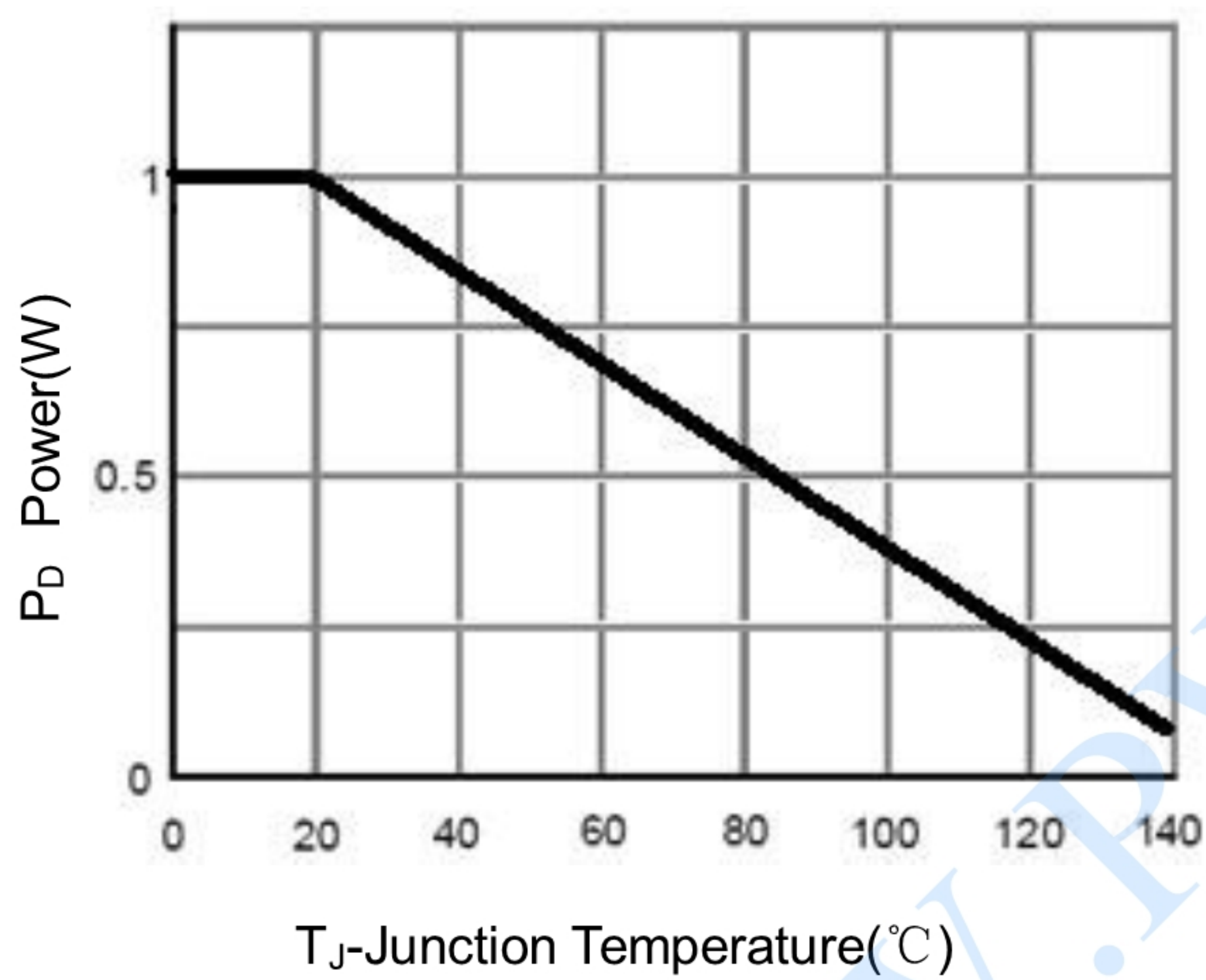


Figure 3 Power Dissipation

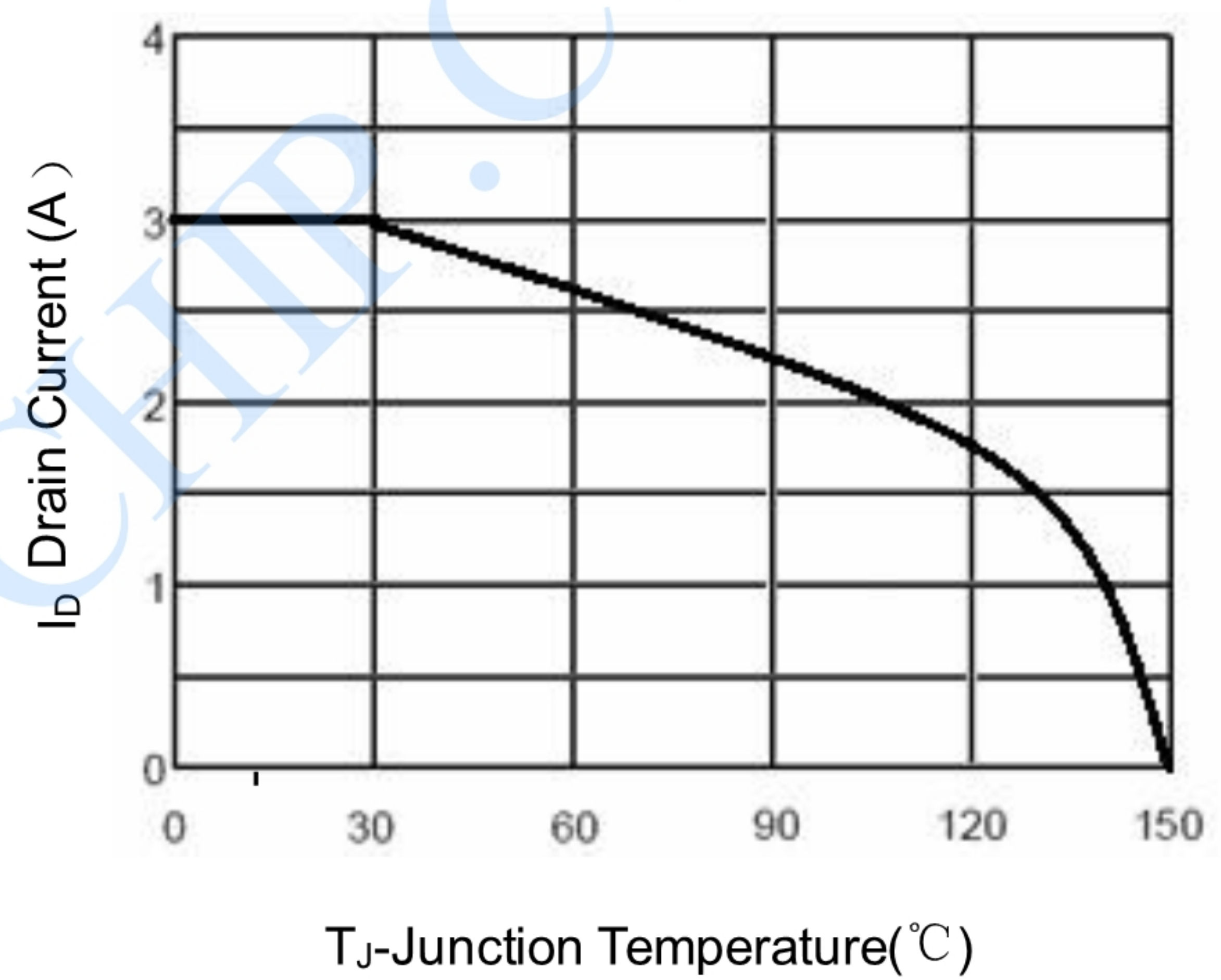


Figure 4 Drain Current

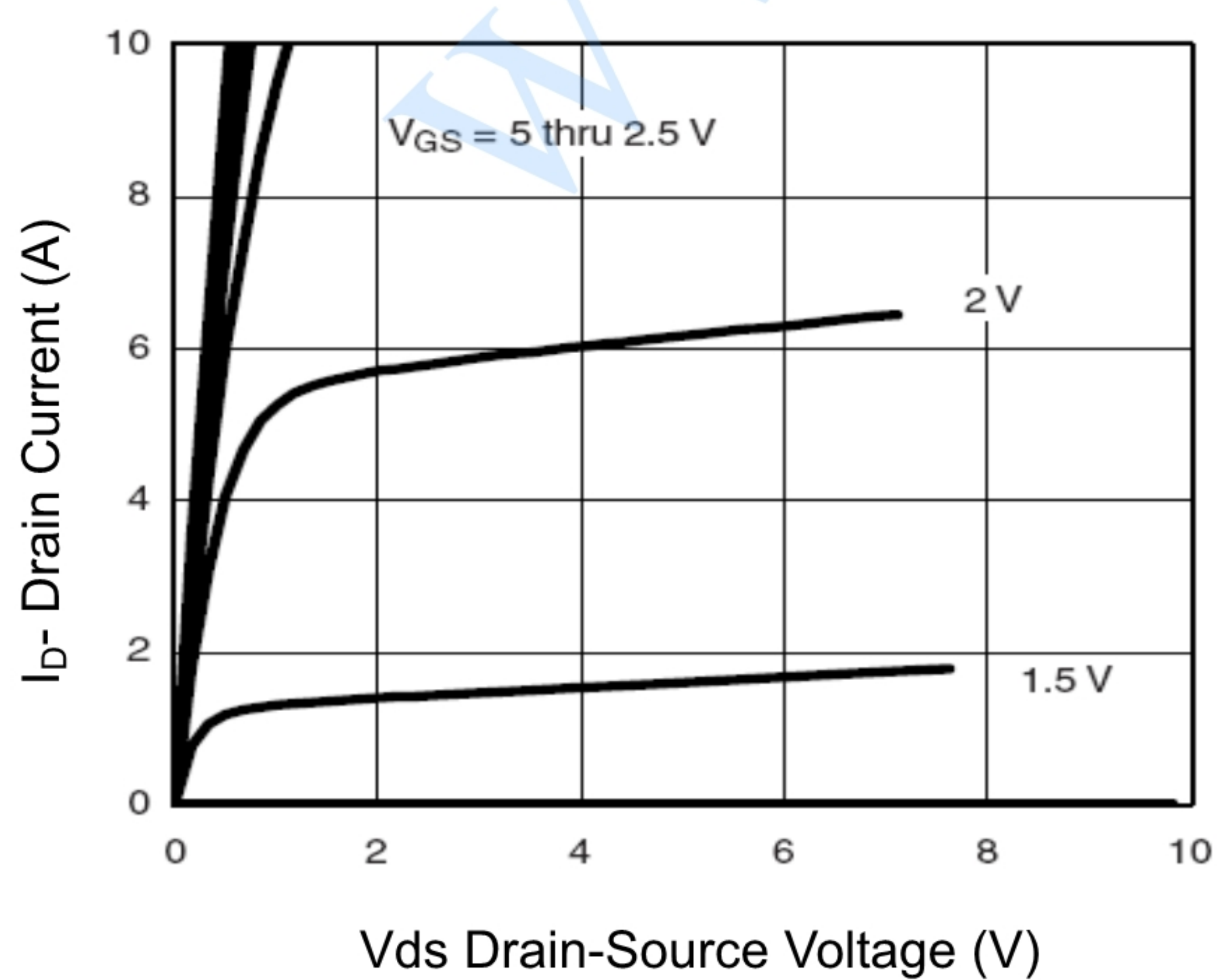


Figure 5 Output Characteristics

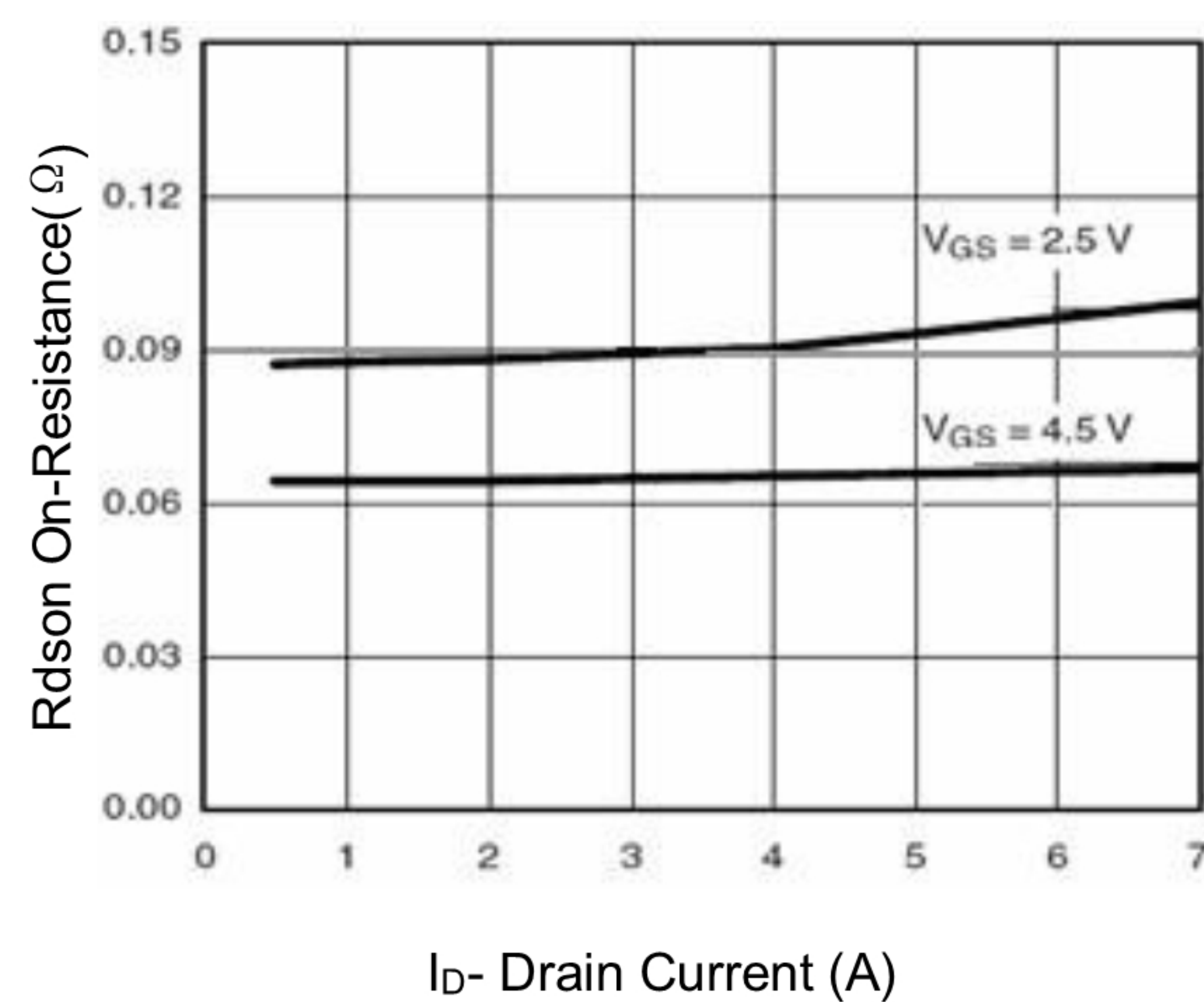


Figure 6 Drain-Source On-Resistance

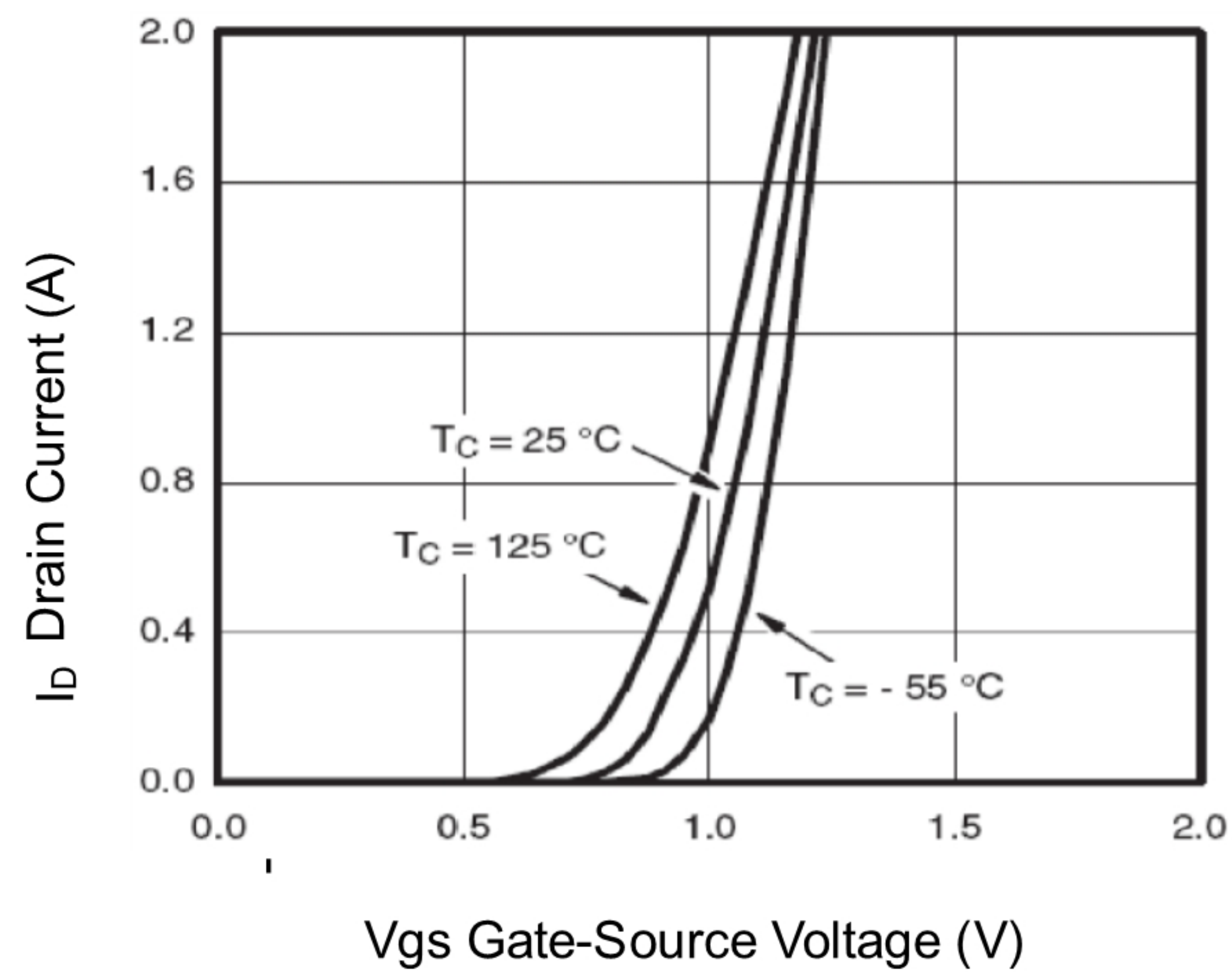


Figure 7 Transfer Characteristics

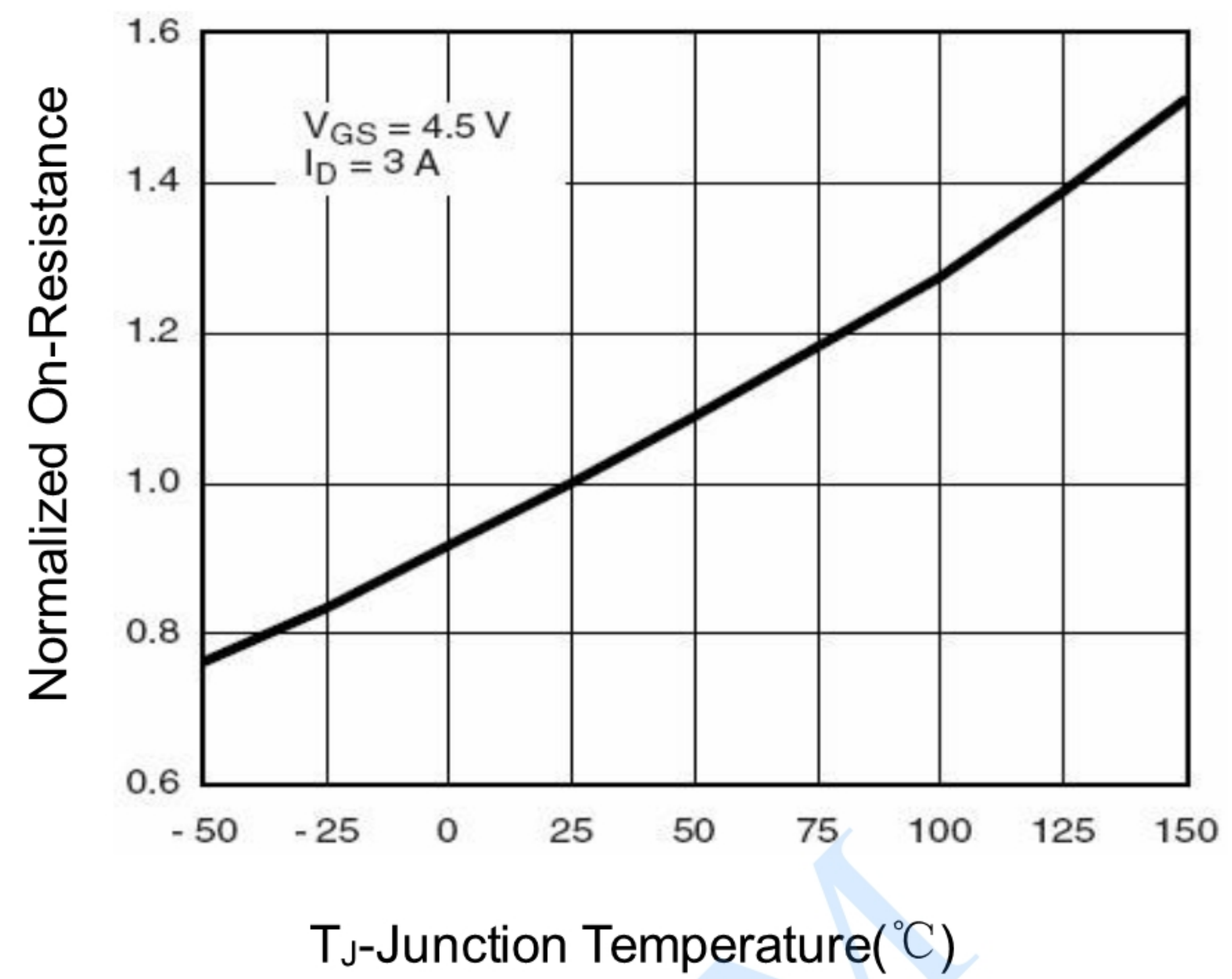


Figure 8 Drain-Source On-Resistance

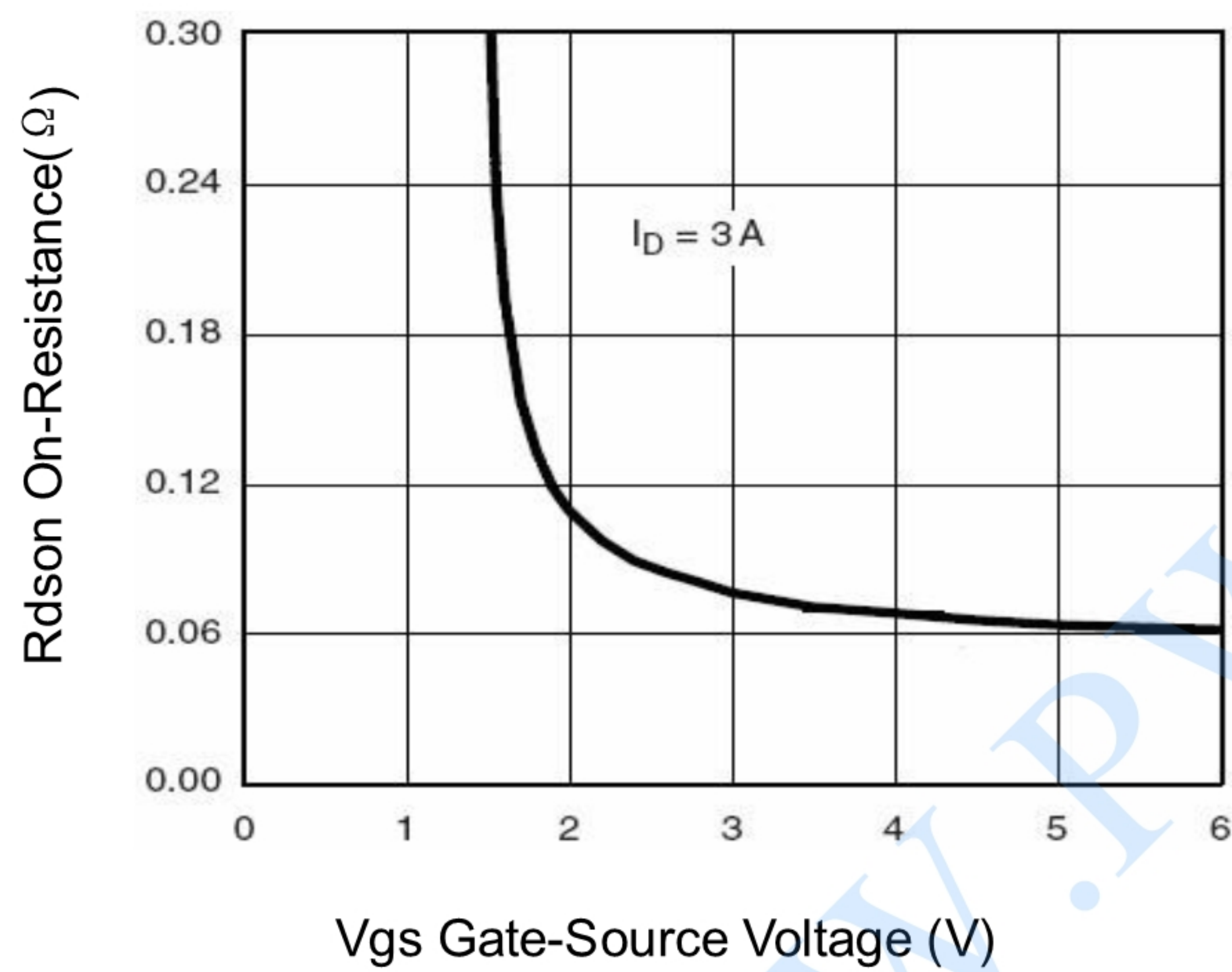


Figure 9 Rdson vs Vgs

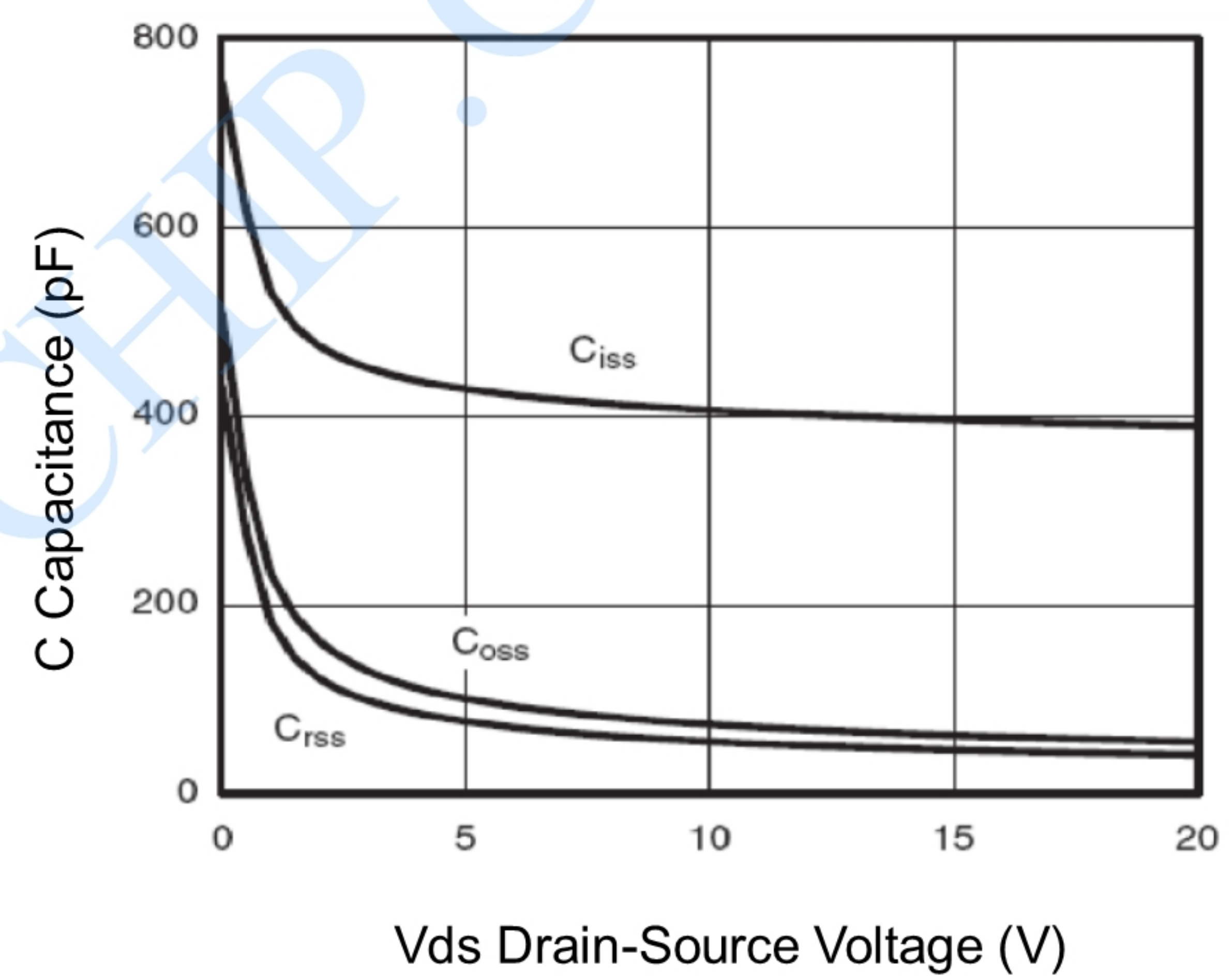


Figure 10 Capacitance vs Vds

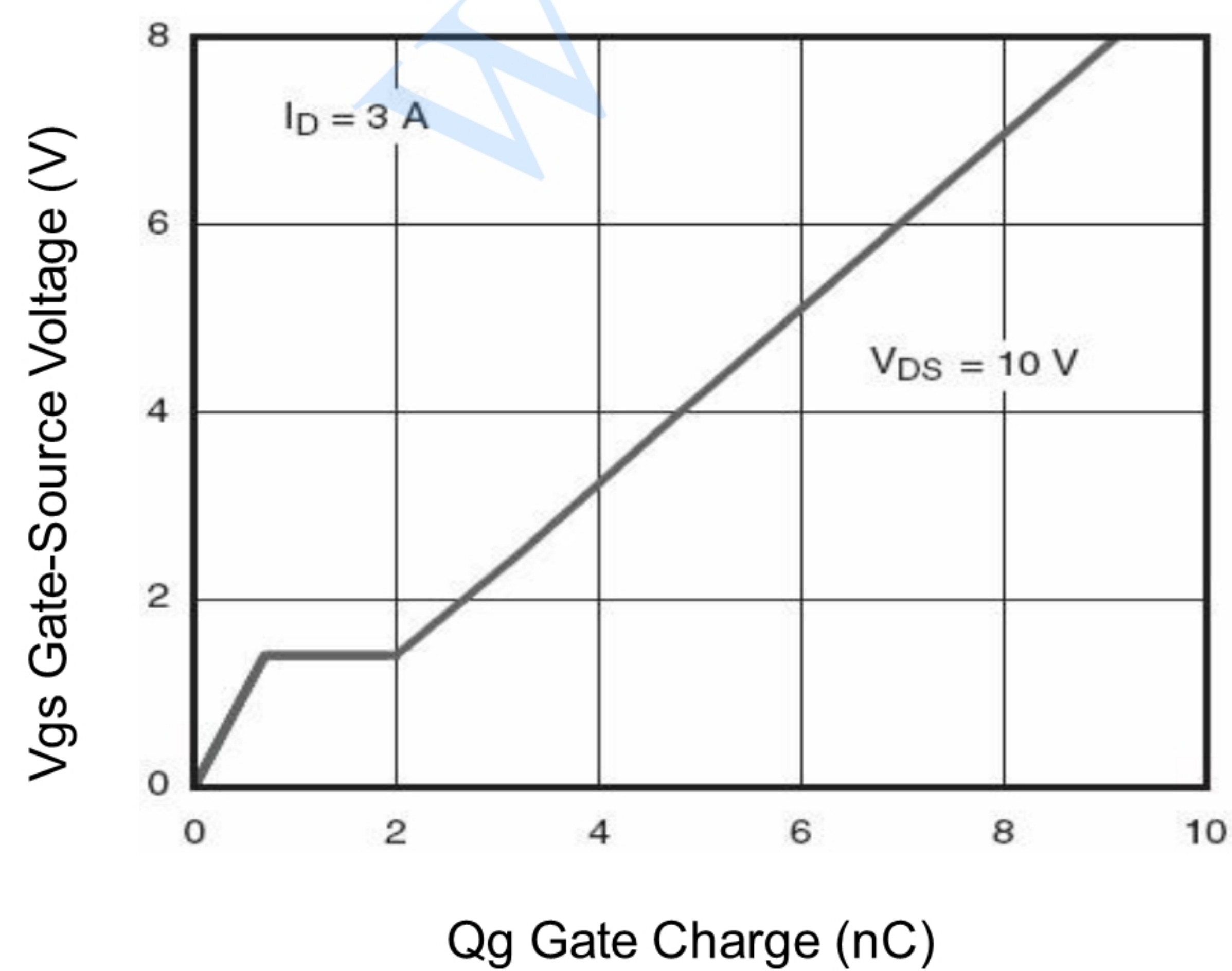


Figure 11 Gate Charge

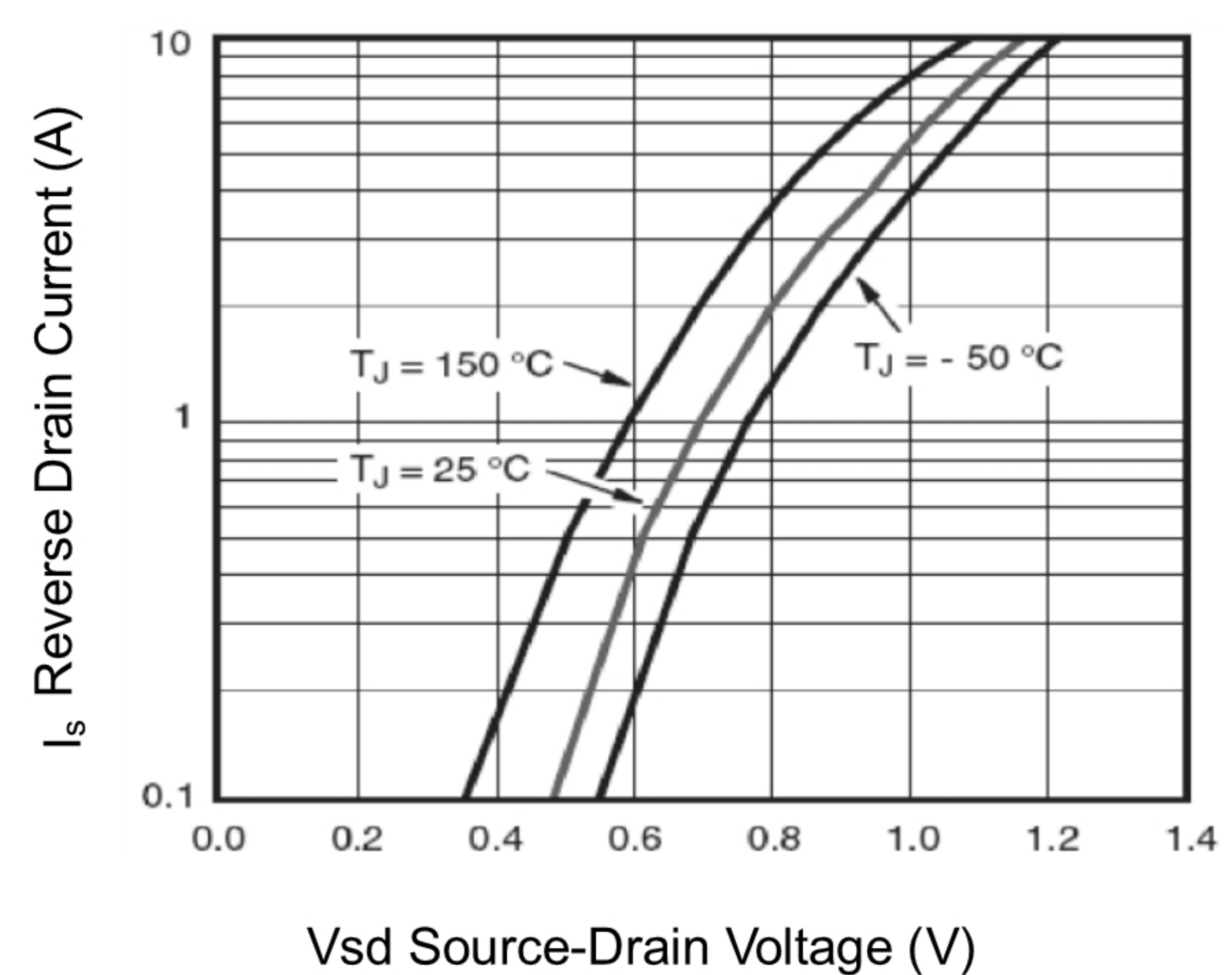


Figure 12 Source- Drain Diode Forward

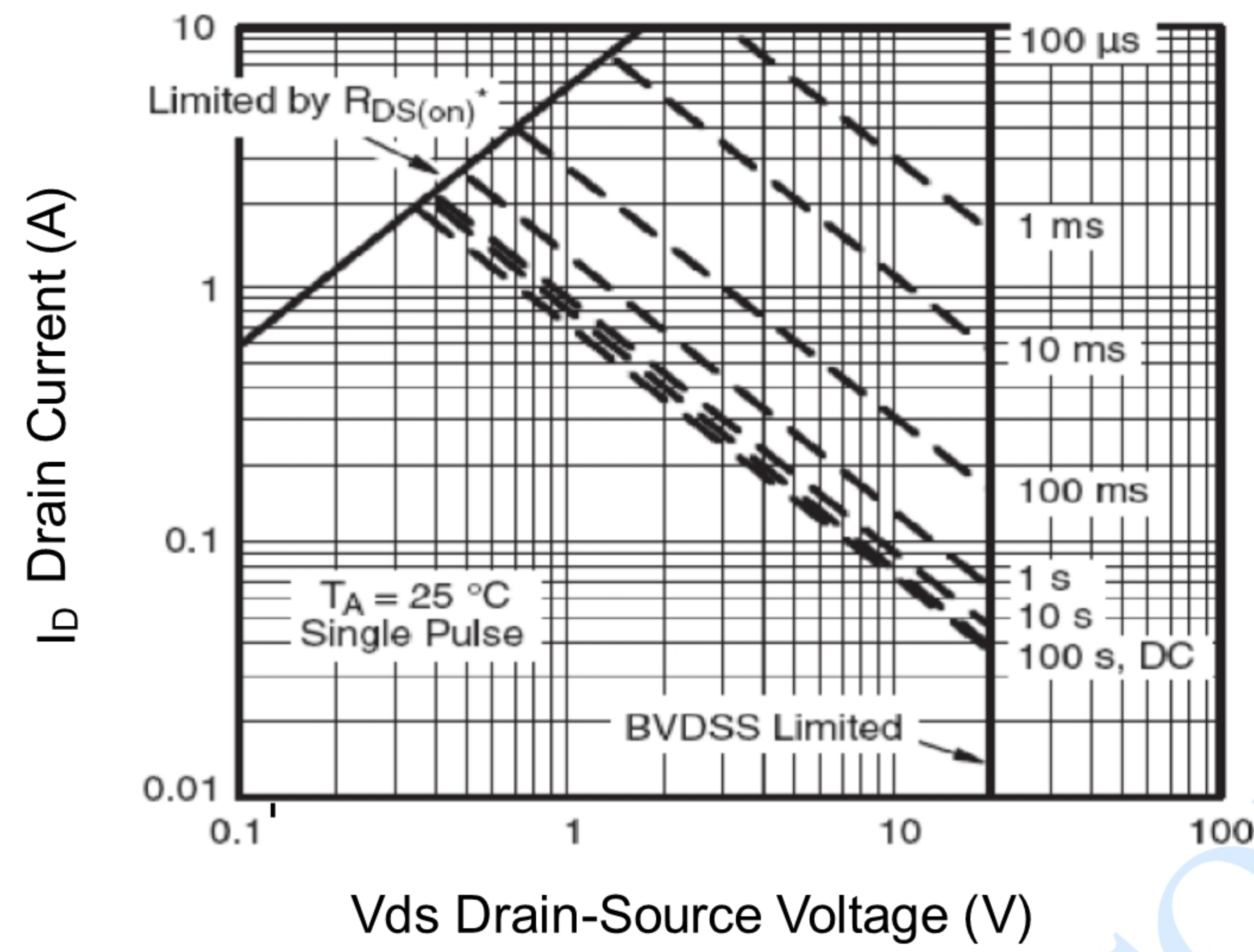


Figure 13 Safe Operation Area

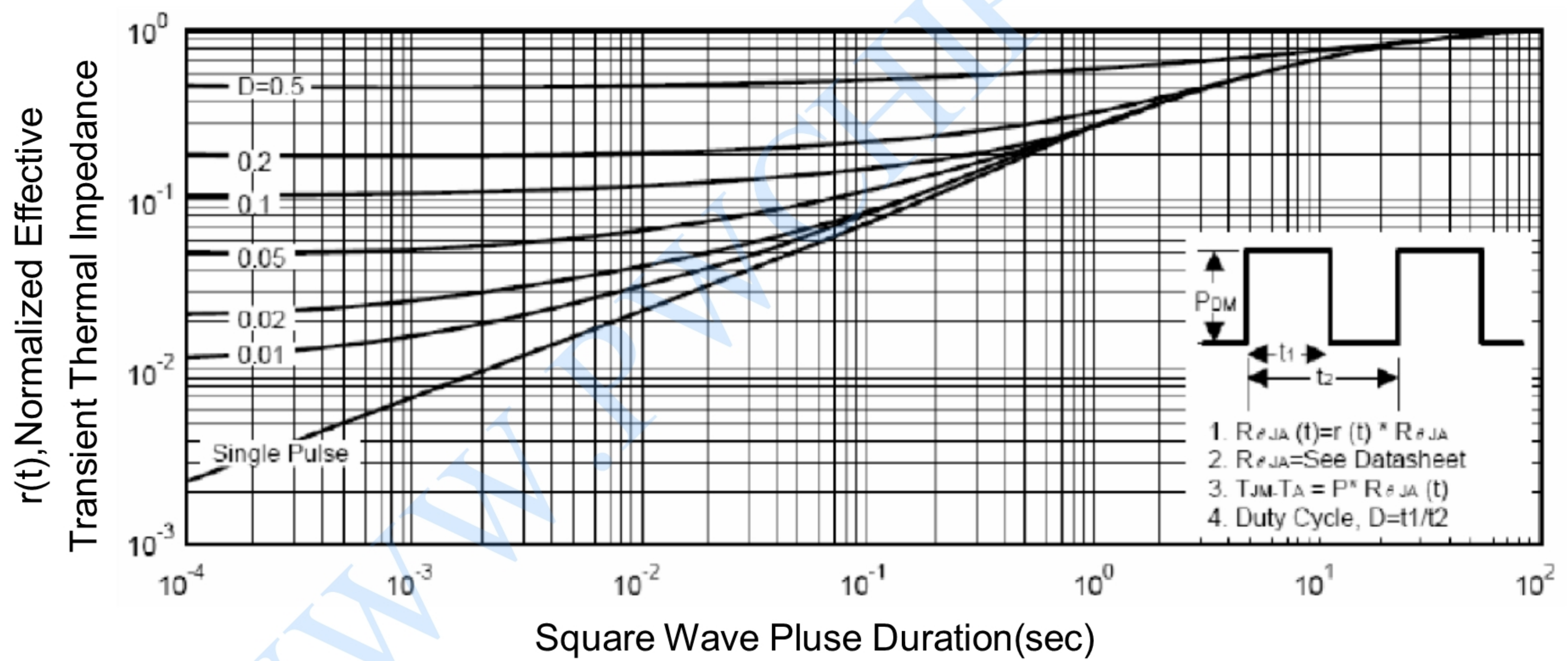


Figure 14 Normalized Maximum Transient Thermal Impedance



Soldering Information

Reflow Soldering:

The choice of heating method may be influenced by plastic QFP package). If infrared or vapor phase heating is used and the package is not absolutely dry (less than 0.1% moisture content by weight), vaporization of the small amount of moisture in them can cause cracking of the plastic body. Preheating is necessary to dry the paste and evaporate the binding agent. Preheating duration: 45 minutes at 45 °C.

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printedcircuit board by screen printing, stenciling or pressure-syringe dispensing before package placement. Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 270 °C depending on solder paste material. The top-surface temperature of the packages should preferable be kept below 245 °C for thick/large packages (packages with a thickness 2.5 mm or with a volume 350 mm³ so called thick/large packages). The top-surface temperature of the packages should preferable be kept below 260 °C for thin/small packages (packages with a thickness < 2.5 mm and a volume < 350 mm³ so called thin/small packages).

Stage	Condition	Duration
1'st Ram Up Rate	max3.0+/-2 /sec	-
Preheat	150 ~200	60~180 sec
2'nd Ram Up	max3.0+/-2 /sec	-
Solder Joint	217 above	60~150 sec
Peak Temp	260 +0/-5	20~40 sec
Ram Down rate	6 /sec max	

Wave Soldering:

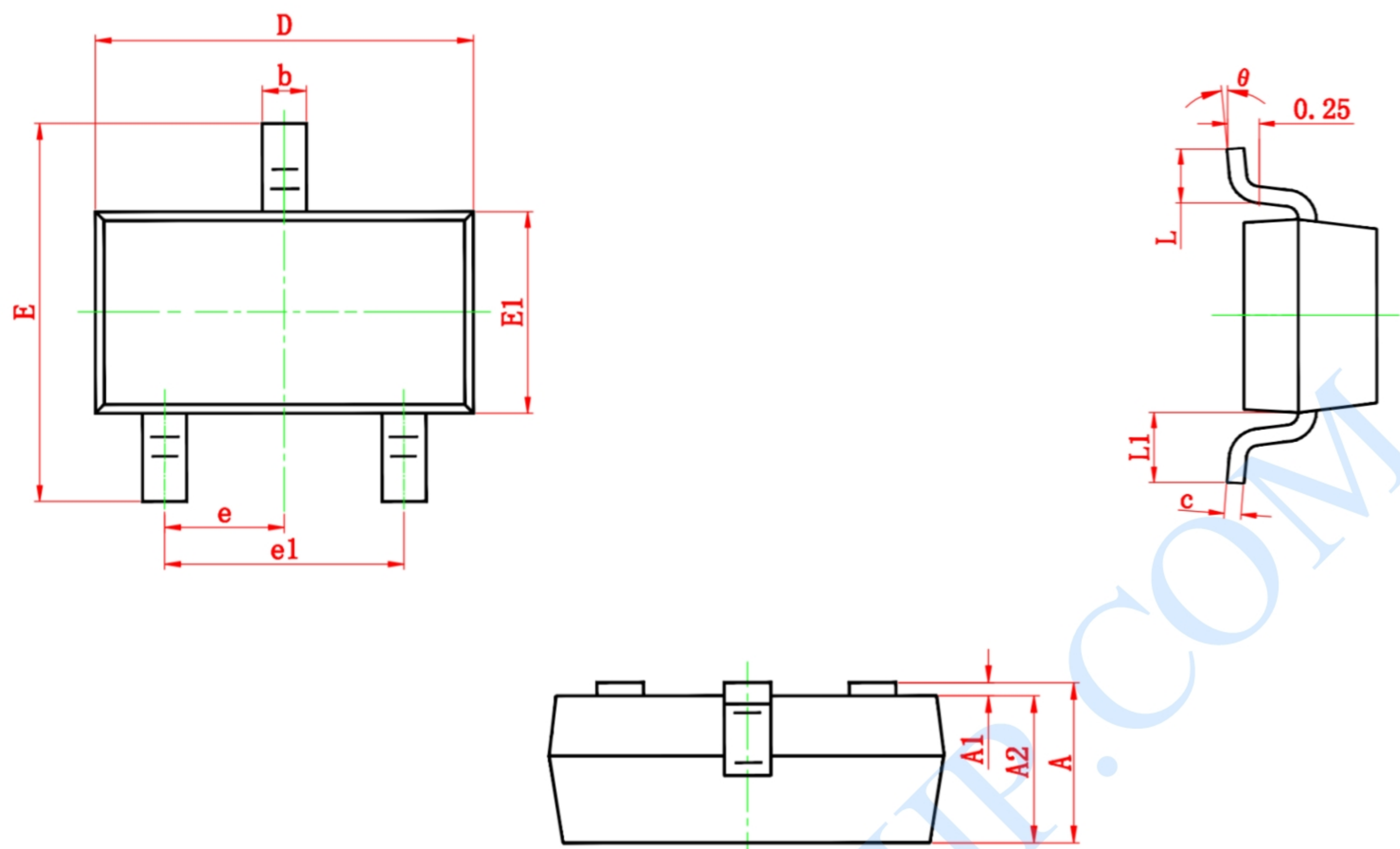
Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

Manual Soldering:

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C. When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.



PACKAGE DESCRIPTION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	2.250	2.550	0.089	0.100
E1	1.200	1.400	0.047	0.055
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.300	0.500	0.012	0.020
L1	0.550 REF.		0.022 REF.	
θ	0°	8°	0°	8°

Notes

1. All dimensions are in millimeters.
2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.



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